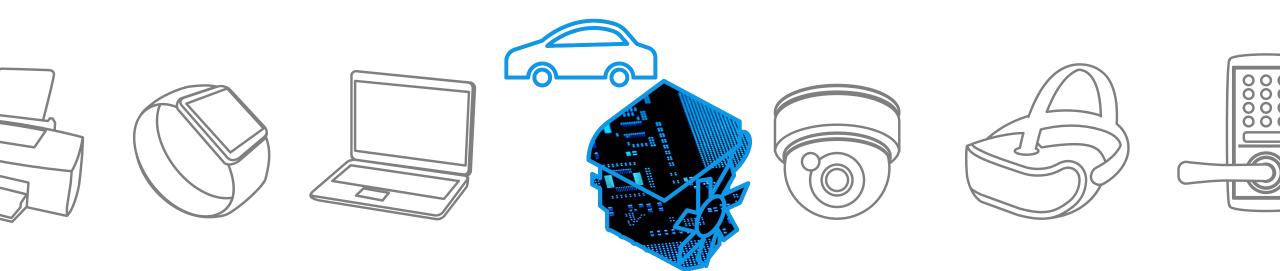
TOSHIBA Automotive Engine Control

Solution Proposal by Toshiba



R20





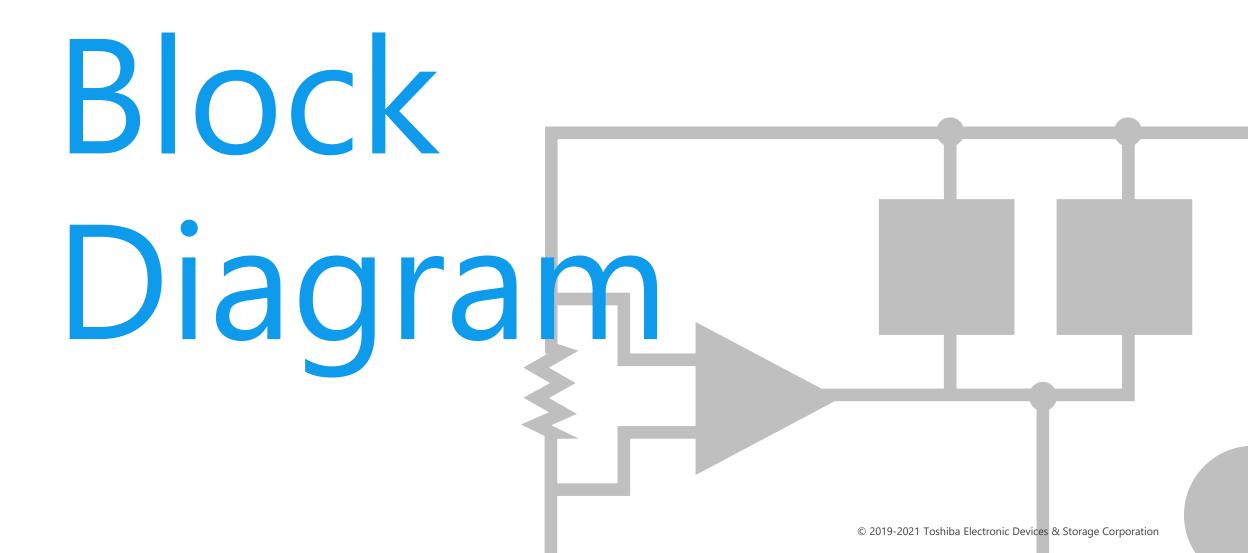


Toshiba Electronic Devices & Storage Corporation provides comprehensive device solutions to customers developing new products by applying its thorough understanding of the systems acquired through the analysis of basic product designs.

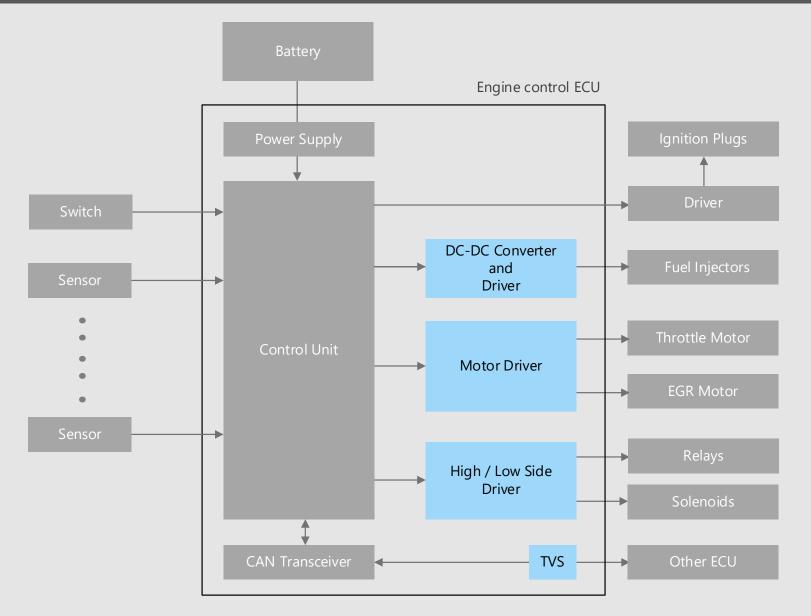




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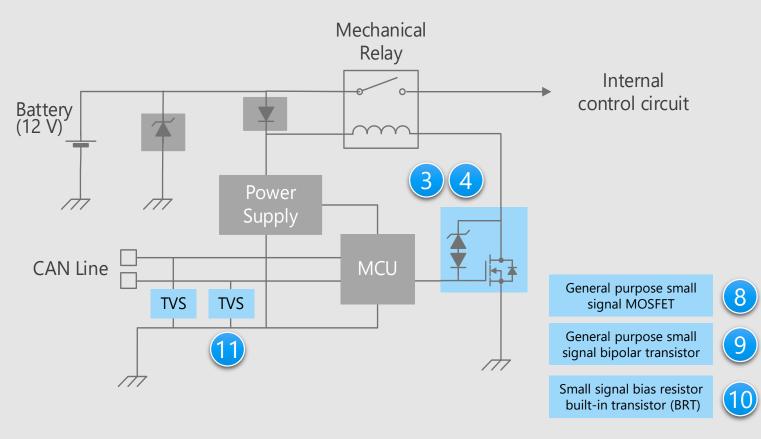


Engine Control Overall block diagram



Engine Control Detail of power management circuit

Mechanical relay type



* Click on the numbers in the circuit diagram to jump to the detailed descriptions page

Criteria for device selection

- It is necessary to select a device that can protect the system from the voltage generated by the back electromotive force (EMF) of inductive loads.
- A small surface mount package is suitable for realizing miniaturization of the ECU.

Proposals from Toshiba

Built-in active clamp circuit and pull-down resistor for relay drive

MOSFET with a built-in active clamp circuit

3

8

9

Driver with protection function -

Low side switch / high side switch (up to 1 A)

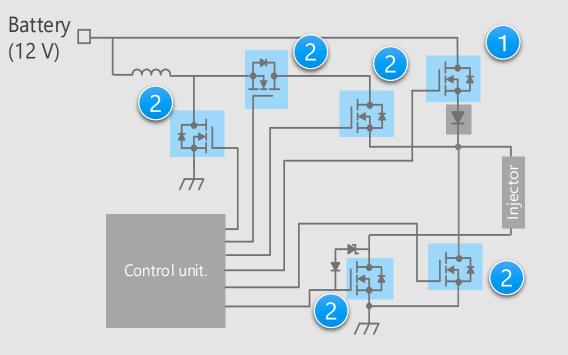
Extensive product lineup

General purpose small signal MOSFET General purpose small signal bipolar transistor Small signal bias resistor built-in transistor (BRT) (10)

Suitable for ESD protection TVS diode (for CAN communication)

Engine Control Detail of injector drive circuit

Fuel injection system



* Click on the numbers in the circuit diagram to jump to the detailed descriptions page

Criteria for device selection

- It is necessary to select the product with the suitable voltage and current ratings for each application.
- A small surface mount package is suitable for realizing miniaturization of the ECU.
- Products with higher breakdown-voltage must be selected according to the power supply voltages.

Proposals from Toshiba

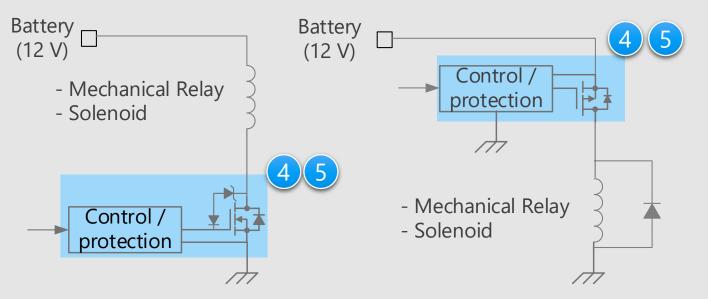
 Low on-resistance contributes low power consumption of the system
 U-MOS Series 40 V N-ch MOSFET
 U-MOS Series 100 V N-ch MOSFET



Engine Control Detail of actuator drive circuit

Low side switch drive circuit

High side switch drive circuit



* Click on the numbers in the circuit diagram to jump to the detailed descriptions page

Criteria for device selection

- It is necessary to select the product with the suitable voltage and current ratings for each application.
- A small surface mount package is suitable for realizing miniaturization of the ECU.

Proposals from Toshiba

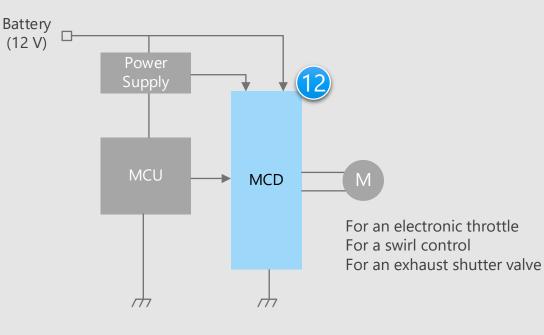
- Driver with protection function

Low side switch / high side switch (up to 1 A) Low side switch / high side switch (1 to 5 A)



Engine Control Detail of motor drive circuit

Motor drive for engine control valves



The number of loading=1 to 3ch

* Click on the numbers in the circuit diagram to jump to the detailed descriptions page

Criteria for device selection

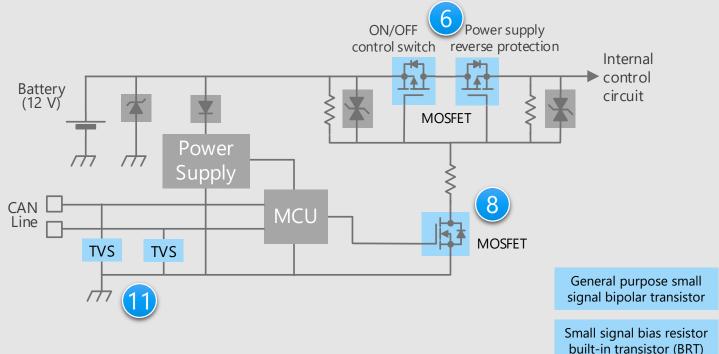
- A small surface mount package is suitable for realizing miniaturization of the ECU.

Proposals from Toshiba
H-bridge driver using PWM
Brushed DC motor driver

12

Engine Control Switch for power supply ON/OFF control and reverse connection protection (1)

Power supply ON/OFF control and reverse connection protection circuit (P-ch type)



* Click on the numbers in the circuit diagram to jump to the detailed descriptions page

Criteria for device selection

- It is necessary to select the product with the suitable voltage and current ratings for each application.
- It is necessary to select a gate driver according to the characteristics of the switching device to be driven.
- A small surface mount package is suitable for realizing miniaturization of the ECU.

Proposals from Toshiba

- Low on-resistance contributes low power
 - consumption of the system

U-MOS Series -40 V / -60 V P-ch MOSFET

Extensive product lineup -

9

General purpose small signal MOSFET 9 General purpose small signal bipolar transistor Small signal bias resistor built-in transistor (BRT) 10

Suitable for ESD protection

TVS diode (for CAN communication)

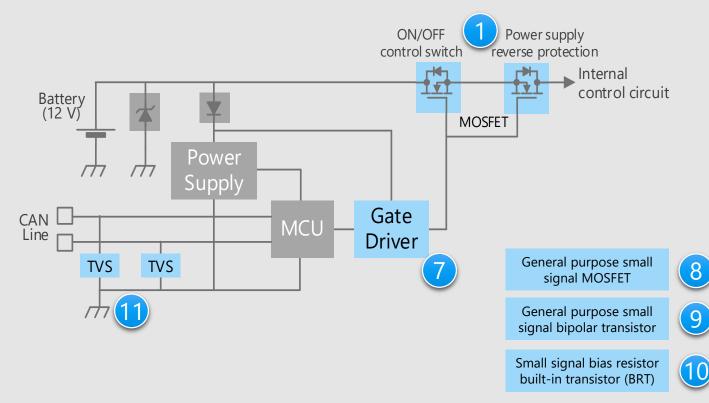


6

8

Engine Control Switch for power supply ON/OFF control and reverse connection protection (2)

Power supply ON/OFF control and reverse connection protection circuit (N-ch type)



* Click on the numbers in the circuit diagram to jump to the detailed descriptions page

Criteria for device selection

- It is necessary to select the product with the suitable voltage and current ratings for each application.
- It is necessary to select a gate driver according to the characteristics of the switching device to be driven.
- A small surface mount package is suitable for realizing miniaturization of the ECU.

Proposals from Toshiba

- Low on-resistance contributes low power consumption of the system
- U-MOS Series 40 V N-ch MOSFET
- Gate driver with built-in protection and diagnosis functions
 - Gate driver (for switch)
- **Extensive product lineup**

General purpose small signal MOSFET General purpose small signal bipolar transistor Small signal bias resistor built-in transistor (BRT)

Suitable for ESD protection

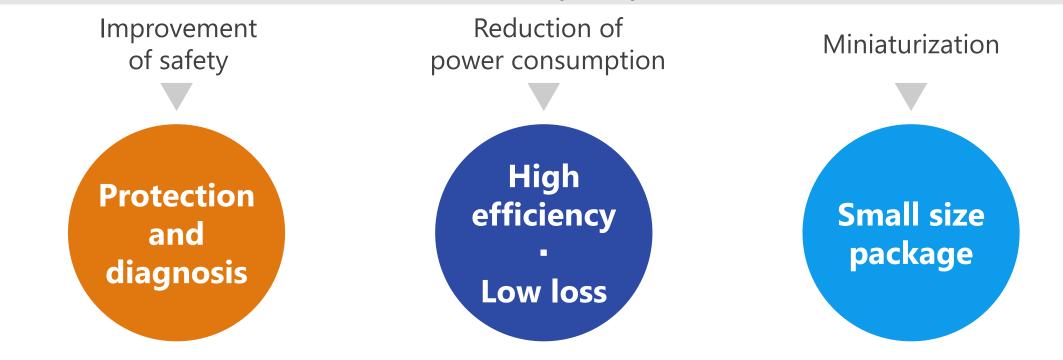
TVS diode (for CAN communication)





Recommended Devices

As described above, in the design of Engine Control, "Improvement of safety", "Reduction of power consumption" and "Miniaturization" are important factors. Toshiba's proposals are based on these three solution perspectives.



Device solutions to address customer needs

	Protection and diagnosis	High efficiency Low loss	Small size package
U-MOS Series 40 V N-ch MOSFET			
2 U-MOS Series 100 V N-ch MOSFET			
3 MOSFET with a built-in active clamp circuit	:		
4 Low side switch / High side switch (up to 1	A)		
5 Low side switch / High side switch (1 to 5 A	A) 🔴		
6 U-MOS Series -40 V / -60 V P-ch MOSFET			
Gate driver (for switch)			
8 General purpose small signal MOSFET			
General purpose small signal bipolar transi	stor		
Small signal bias resistor built-in transistor	(BRT)		
1 TVS diode (for CAN communication)			
Brushed DC motor driver			

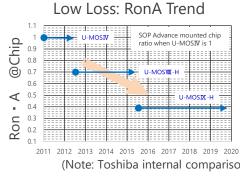


The advanced U-MOSIX-H processes enables low on-resistance and low noise, thereby reducing power consumption.

Low loss (reduced on-resistance)

Using low on-resistance technology to contribute to reduced power consumption systems.

On-resistance of 61 % reduction per unit area. (compared to U-MOSIV)



TO-220SM(W) Cu cor



Packag reduced by 64 %, compared to D2PAK+.



Low-noise. Switching waveform

Compact and low loss package

By adopting a Cu connector structure and a double-sided heat dissipation structure, low loss and high heat dissipation are realized. Wettable Frank (WF) package contributes good mountability.

Low V_{DS} peak



Low noise (low EMI)

Improved chip process reduces surge voltage and ringing time.

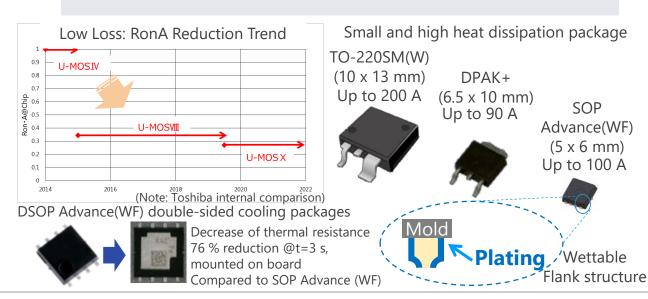
(includ	LOW-HOISE. SWITCHII						
dvance mounted chip then U-MOSIV is 1	J-MOSVIII-H		ш-н Line up				
	$V_{GS} : 2 V/div$ $V_{DS} : 5 V/div$ $V_{DS} : 2 A/div$	V _{GS} : 2 V / div V _{DS} : 5 V / div	Part number	Drain current	On-resistance (Max) @V _{GS} = 10 V	Package	
+++	t : 400 ns / div	I _{DS} : 2 A / div ++++++++++++++++++++++++++++++++++++	XPN3R804NC	40 A	3.8 mΩ	TSON Advance(WF)	•
U-MOSIX-H	Ringing time : 802 ns	Ringing time : 468 ns	TK1R4S04PB	120 A	1.35 mΩ	DPAK+	
	/ M		TPHR7904PB	150 A	0.79 mΩ	SOP Advance(WF)	•
2017 2018 2019 2020 ernal comparison)			TPWR7904PB	150 A	0.79 mΩ	DSOP Advance(WF)L	\diamond
onnector design	DSOP Advance(WF)	L double-sided cooling pack		250 A	0.74 mΩ	TO-220SM(W)	
5		Thermal resistance is reduced		160 A	1.5 mΩ	D2PAK+	
age resistance is		by 76 % $@t = 3 s$,	4				



Low on-resistance contributes to reduced system power consumption.

Low loss (reduced on-resistance)

Using low resistance wafer process technology to contribute to reduced power consumption systems.



Si

Small and high heat dissipation package

Development of small and high heat dissipation packages by adopting a Cu connector structure. Ensuring mountability by using the Wettable Flank (WF) structure.

Line up			
Part number	Drain current	ON-resistance (Max) @V _{GS} = 10 V	Package
XPN2400ANC *	20 A	23.5 mΩ	TSON Advance(WF)
TK60S10N1L	60 A	6.11 mΩ	DPAK+
XPH4R10ANB	70 A	4.1 mΩ	SOP Advance(WF)
XPW4R10ANB	70 A	4.1 mΩ	DSOP Advance(WF)
TK160F10N1L	160 A	2.4 mΩ	
XK1R9F10QB	160 A	1.92 mΩ	TO-220SM(W)
XK4R0F10QB *	(60 A)	(4.0 mΩ)	

*: Under Development (The specification is subject to change without notice.)



These devices have a built-in active clamp circuit to reduce the number of components and to save mounting area.

Built-in active clamp circuit

MOSFET with a built-in active clamp circuit which connected a zener diode between the drain and gate terminals prevents damage caused by voltage surges generated by inductive loads such as a mechanical relay.



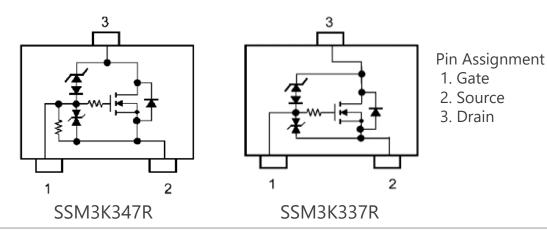
SSM3K347R has built-in 47 k Ω pull-down resistor between the gate and source terminals, thus contributes to reduction of number of components and mounting area.



Low voltage drive

These devices can be driven at low gatesource voltage of 4.0 V.

Internal circuit



Line up					
Part numbe	er	SSM3K347R	SSM3K337R		
Package		SOT-23F	SOT-23F		
V _{DS(DC)} [V]		38	38		
I _D [A]		2	2		
$R_{DS(ON)}$ [m Ω]	Тур.	350	161		
$\begin{array}{c c} R_{DS(ON)} [m\Omega] & Typ. \\ @V_{GS} = 4.0 V & Max \end{array}$		480	200		
Polarity		N-ch	N-ch		





Various protection and diagnostic output functions are built in, contributing to improve reliability and to miniaturize the system.

Built-in various protection and diagnostic output functions

Overcurrent and overheat protection and diagnostic output (except TPD1044F) to the MCUs or the control circuits are built in. These functions contribute to improve reliability of the system.



It is possible that Direct control by output signal of MCUs or CMOS logic ICs.

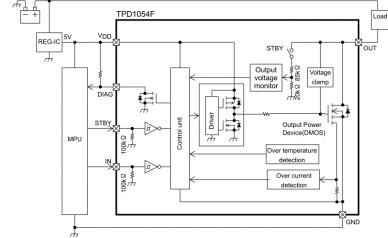


Small package

PS-8 is small surface mount package. It contributes to the miniaturization of system.

Example of low side switch application (Block diagram of TPD1054F)

Suitable for applications with small current load below 1 A, such as mechanical relay



Function	Low si	de switch	High side switch
Part number	TPD1044F	TPD1054F	TPD1052F
Package		PS-8 (2.8 x 2.9 mm)	
Features	 Overcurrent / over- temperature protection Active clamp On-resistance: 0.6 Ω 	 Overcurrent / over- temperature protection Active clamp Diagnostic output function On-resistance: 0.8 Ω 	 Overcurrent / over- temperature protection Diagnostic output function On-resistance: 0.8 Ω



Various protection and diagnostic output functions are built in, contributing to improve reliability and to miniaturize the system.

Built-in various protection and diagnostic output functions

Overcurrent and overheat protection and diagnostic output to the MCUs or the control circuits are built in. These functions contribute to improve reliability of the system.

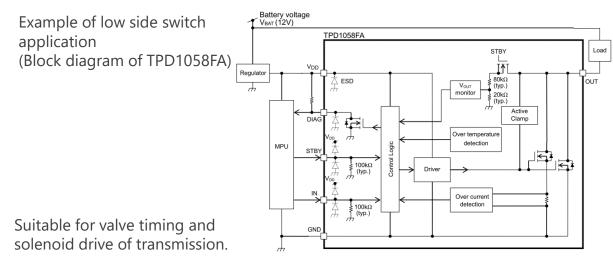


It is possible that Direct control by output signal of MCUs or CMOS logic ICs.



Small package

WSON10 is small surface mount package. It contributes to the miniaturization of system.



Function	Low side switch	High side switch
Part number	TPD1058FA	TPD1055FA
Package	Back surface WSON10	(3 x 3 mm)
Features	 Overcurrent / Overtemperature protection Active clamp Diagnostic output function ON-resistance: 0.1 Ω 	 Overcurrent / Overtemperature protection Diagnostic output function ON-resistance: 0.12 Ω



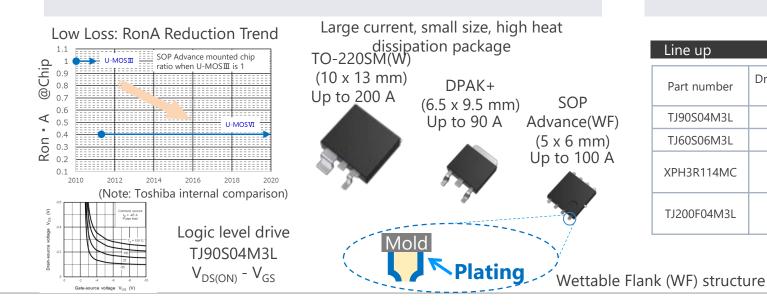


Low on-resistance contributes to reduce system power consumption.

Low loss (reduced on-resistance) and logic level drive

Using low on-resistance technology contributes to reduce system power consumption.

Lineups of logic level drive type are supported.



Small

Small surface mount package developed

By adopting a Cu connector structure and a double-sided heat dissipation structure, low loss and high heat dissipation are realized.

Wettable Frank (WF) package contributes good mountability.

Line up				
Part number	Drain-source Voltage	Drain current	On-resistance (Max) @V _{GS} = -10 V	Package
TJ90S04M3L	-40 V	-90 A	4.3 mΩ	DPAK+
TJ60S06M3L	-60 V	-60 A	11.2 mΩ	DPAK+
XPH3R114MC	-40 V	-100 A	3.1 mΩ	SOP Advance(WF)
TJ200F04M3L	-40 V	-200 A	1.8 mΩ	TO-220SM(W)



Protection and diagnosis Low loss Small size package

Value provided

A charge pump circuit for the N-channel MOSFET gate drive is built in, allowing for easy semiconductor relay configuration.

Built-in charge pump circuit

Built-in charge pump circuit enables Nchannel MOSFET as high side switch. Easy to configure a semiconductor relay. Can be controlled by logic level voltage

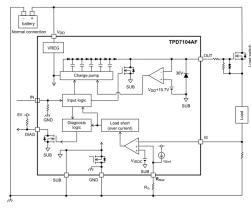
It is possible that Direct control by output signal of MCUs or CMOS logic ICs.



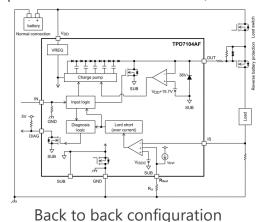
Small package

The small surface mount packages such as PS-8, SSOP16 and WSON10A contribute to the miniaturization of equipment.

Semiconductor relay (switch) application (TPD7104AF)



Power supply reverse connection protection MOSFET control (TPD7104AF)



Line up

Part number	TPD7104AF	TPD7106F	TPD7107F
Package	PS-8 (2.8 x 2.9 mm)	SSOP16 (5.5 x 6.4 mm)	WSON10A (3 x 3 mm)
Features	 Operating power supply voltage range: 5 to 18 V Built-in power supply reverse connection protection function (Supported for power supply reverse connection protection MOSFET applications) 	 Operating power supply voltage range: 4.5 to 27 V Built-in power supply reverse connection protection function (Supported for power supply reverse connection protection MOSFET applications) 	 Operating power supply voltage range: 5.75 to 26 V Current sense output Protective functions; overcurrent, overtemperature, GND disconnect, etc. reverse battery connection Diagnosis output; overcurrent, load open, overtemperature, etc.





Wide lineup of small packages contribute to reduce the size and power consumption of system.

Small package

A lineup of various small packages such as SOT-723 (VESM 1.2 x 1.2 mm package) is available, contributing to reduce mounting area.

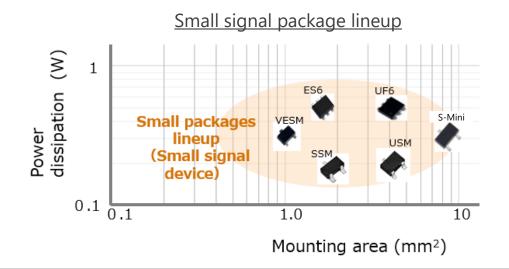


SSM3J66MFV can be driven at low gatesource voltage of 1.2 V.



AEC-Q101 qualified

AEC-Q101 qualified and can be used for various automotive applications.



Line up

Part number	Part number		SSM3J168F	SSM3J66MFV
Package		S-Mini (SOT-346)	S-Mini (SOT-346)	VESM (SOT-723)
V _{DSS} [V]	V _{DSS} [V]		-60	-20
I _D [A]		0.4	-0.4	-0.8
R _{DS(ON)}	Тур.	1.2	1.4	0.31
@ V _{GS} =4.5 V [Ω]			1.9	0.39
Drive voltage [\	Drive voltage [V] 4.5 -4.0		-1.2	
Polarity		N-ch	P-ch	P-ch





Extensive product lineup to meet customers' needs.

Extensive lineup of packages

Various packages such as 1-in-1, 2-in-1 are provided and suitable products for circuit board design are selectable.

Extensive product lineup

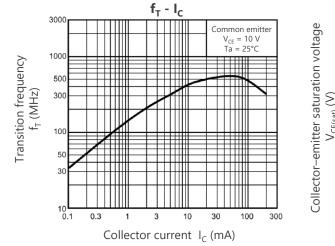
Various product lineups, such as general purpose, low noise, low $V_{CE(sat)}$ and high current types are provided. Products can be selected in accordance to the application.

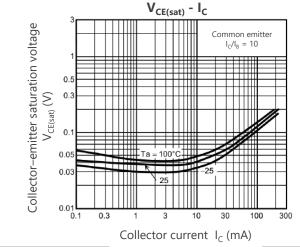


AEC-Q101 qualified

AEC-Q101 qualified and can be used for various automotive applications.

Characteristic examples of 2SC2712





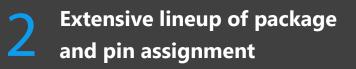
Line up								
Рас	kage		SOT	-23F		OT-323) DT-323F)*	S-Mini (S	SOT-346)
Classification	$ V_{CEO} $ [V]	l _c [mA]	NPN	PNP	NPN	PNP	NPN	PNP
Conoral purposa	50	150			2SC4116	2SA1586	2SC2712	2SA1162
General purpose	50	500					2SC3325	2SA1313
Low noise	120	100			2SC4117	2SA1587	2SC2713	2SA1163
	50	1700				2SA2195*		
High current	50	2000		TTA501				
	100	2500	TTC501					



Extensive product lineup to meet customers' needs.

Built-in bias resistor type (BRT : Bias Resistor built-in Transistor)

The BRTs contribute to reduction of the number of components, assembly workload and mounting area of circuit boards.

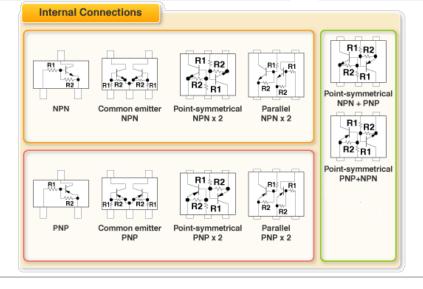


Various package lineups, such as 1-in-1, 2-in-1 and various pin assignment type are provided and suitable products for circuit board design are selectable.



AEC-Q101 qualified

AEC-Q101 qualified and can be used for various automotive applications.



Line up					
	Part number	NPN (BRT)	PNP (BRT)		
Packago	ES6 (SOT-563)	RN1907FE	RN2907FE		
Package	US6 (SOT-363)	RN1901	RN2901		
	V _{CEO} (Max) [V]	50	-50		
	I _C [mA]	100	-100		





TVS diodes prevent system damage and malfunction caused by electrostatic discharge (ESD).

Improve ESD pulse absorbability

Toshiba proprietary Zener process improves the ESD pulse absorption of TVS diodes. (Both low dynamic resistance R_{DYN} and low capacitance between terminals C_t)

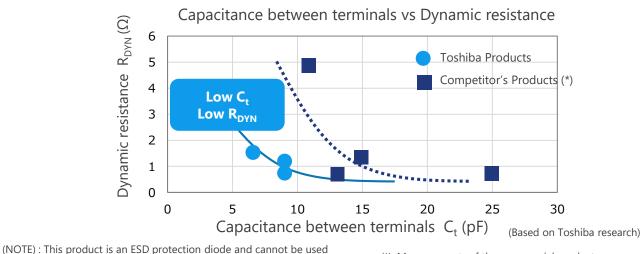
2 Supports CAN, CAN FD and FlexRay

These are products applicable to invehicle LAN communication such as CAN, CAN FD and FlexRay.



High ESD immunity

 $V_{ESD} > \pm 30 \text{ kV} @$ ISO 10605 $V_{ESD} > \pm 20 \text{ kV}$ (L4) @ IEC61000-4-2



for purposes other than ESD protection.

(*): Measurements of the commercial product

Line up				
Part number	DF3D18FU	DF3D29FU	DF3D36FU	
Package	USM (SOT-323)			
V _{ESD} [kV] @ISO 10605	±30	±30	±20	
V _{RWM} (Max) [V]	12	24	28	
C _t (Typ. / Max) [pF]	9 / 10 6.5 / 8			
R _{DYN} (Typ.) [Ω]	0.8	1.1	1.5	



Protection and diagnosis High efficiency Low loss Small size package

Value provided

This is a brushed DC motor driver IC packaged in a compact package to control the engine throttle valve and other engine valves.

PWM type 1ch H-bridge driver

High efficiency drive is realized by PWM controlling of H-bridge consist of P-ch and N-ch DMOS with low on-resistance.

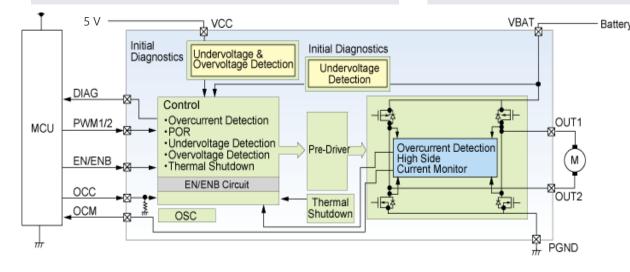


Over current detection, over temperature detection, VCC high voltage detection and VCC low voltage detection function are built in. In addition, through current protection circuit is also built in.



Small package

PQFN28 (6 x 6 mm) package contributes to miniaturization of ECU.



Line up				
Part number		TB9051FTG		
Package		PQFN28		
Operating voltage range [V]		4.5 to 28		
Over current / Over temperature detection		\checkmark		
Diagnostics		\checkmark		
$\begin{array}{c} R_{ON(Pch+Nch)} \\ @V_{BAT} = 8 \text{ V, T}j = 150 \text{ °C } [\Omega] \end{array}$	Max	0.45		
Output current [A]	Max	5		



High Protection Small size efficiencv and package diagnosis Low loss

Value provided

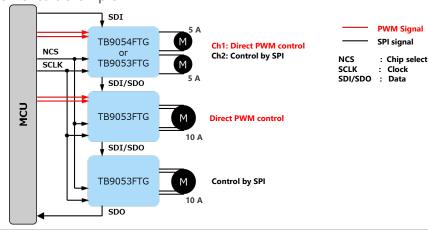
These 2ch H-bridge driver ICs packaged in the compact packages can drive and control brushed DC motor through the SPI (Serial Peripheral Interface) registers.

5 A rating ^[Note1], PWM type **2ch H-bridge driver**

2 channels of H-bridge driver with 5 A rating [Note 1] composed of low on-resistance DMOS FETs are built in. 10 A rating [Note 1] 1 channel drive with 2 channel parallel connection is also possible.

> [Note1] The value will be limited smaller by the condition such as environment temperature or battery voltage

Application circuit example





Daisy chain connection and SPI communication contribute to reduction of MCU port number or increasing flexibility of system design.

M Signa

Line up



Small package

TB9053FTG is packaged in P-QFN40 package with high heat dissipation, and TB9054FTG is packaged in P-VQFN40 package with wettable frank structure. These contribute to the miniaturization of ECUs.

Part number		TB9053FTG		TB9054FTG	
Package		P-QFN40 (6 x 6 mm)	-	P-VQFN40 (6 x 6 mm)	
Operating voltage range [V]		4.5 to 28			
Over current / Over temperature detection		\checkmark			
Diagnostics		\checkmark			
$\begin{array}{l} R_{ON(Nch+Nch)}\\ @V_{BAT}=8~V,~Tj=150~^\circC~[\Omega] \end{array}$	Max	0.35			
Output current [A]	Max	5 (x 2ch)			

If you are interested in these products and have questions or comments about any of them, please do not hesitate to contact us below:

Contact address: https://toshiba.semicon-storage.com/ap-en/contact.html

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